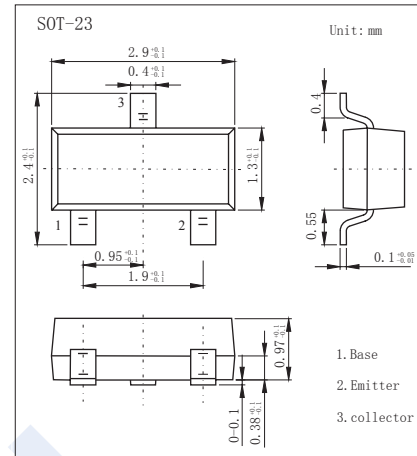


NPN Transistors

2SC2618

■ Features

- Collector Current Capability $I_C=500\text{mA}$
- Collector Emitter Voltage $V_{CE0}=35\text{V}$
- Complementary to 2SA1121



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	35	V
Collector - Emitter Voltage	V_{CE0}	35	
Emitter - Base Voltage	V_{EB0}	4	
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100 \mu\text{A}, I_E = 0$	35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1\text{mA}, I_B = 0$	35			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_C = 0$	4			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 20\text{V}, I_E = 0$			0.5	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 4\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$			0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 3\text{V}, I_C = 10\text{mA}$		0.64		
DC current gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 10\text{mA}$	60		320	
		$V_{CE} = 3\text{V}, I_C = 500\text{mA}$	10			

■ Classification of $h_{FE}(1)$

Type	2SC2618-B	2SC2618-C	2SC2618-D
Range	60-120	100-200	160-320
Marking	RB	RC	RD